

Notice of References CitedApplication No.
09/241,695Applicant(s)
Miyanaga et al.Examiner
Shouxiang HuGroup Art Unit
2811

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	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	5,893,740	4/13/99	Chang et al.	438	289
B	5,926,712	7/20/99	Chen et al.	438	291
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K					
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M					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N						
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NON-PATENT DOCUMENTS

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U	Son et al., "Comparative Study of Several Anti-Punchthrough Designs for Buried Channel PMOSFET, " Device Reserach Conference Digest	6/97
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